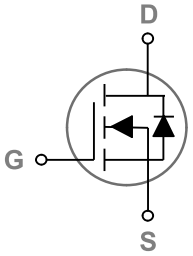
Features

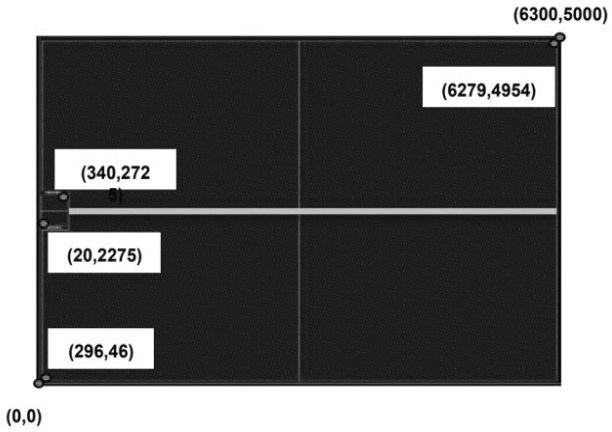
- *Die in 8" Wafer Form*
- *150V , N-Channel*
- *$R_{DS(ON)}$=4.3mΩ (Max.) @ V_{GS}=10V*

Applications

- Networking
- Load Switch
- LED applications
- Quick Charge



Die Description

Parameter	Parameter	Rating	CHIP DRAWING
Die Size (with SL)	6360 X 5060	um²	
Gate Pad Size	320 X 450		
Source Pad Size	Full Metalized Source Region		
Scribe Line Size	60	um	
Wafer size	200	mm	
Wafer Thickness	8 (±0.8)	mil	
Top Metallization	4um , Al-Cu		
Back Metallization	Ti/Ni/Ag (1/3/10 KÅ)		
Gate Bond Wire	5 mil Al x 1		
Source Bond Wire	20 mil Al Stitch x 5		
Estimated Gross Die	850		

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	150V	V
V_{GSS}	Gate-Source Voltage	±20V	V
T_J	Operating Junction Temperature Range	-55 to 150℃	℃
T_{STG}	Storage Temperature Range	-55 to 150℃	℃

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	150	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=120V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=120V , V_{GS}=0V , T_J=85℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=30A	---	3.6	4.3	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2	3	4	V

Note：1.RDSON calculated by TOLL Single Package Type.